

## IGBT

Symbol	Test Conditions	Maximum Ratings	Unit
<b>V<sub>CES</sub></b> <b>V<sub>CGR</sub></b>	T <sub>J</sub> =25°C to 150°C T <sub>J</sub> =25°C to 150°C; R <sub>GE</sub> =1 MΩ;	1200 1200	V
<b>V<sub>GES</sub></b> <b>V<sub>GEM</sub></b>	Continuous Transient	±20 ±30	V
<b>I<sub>C25</sub></b> <b>I<sub>C100</sub></b> <b>I<sub>CM</sub></b>	T <sub>C</sub> =25°C; limited by leads T <sub>C</sub> =100°C T <sub>C</sub> =25°C, 1 ms	80 40 160	A
<b>SSOA</b> <b>(RBSOA)</b>	V <sub>GE</sub> =15V; T <sub>VJ</sub> =125°C; R <sub>G</sub> =5 Ω Clamped inductive load	I <sub>CM</sub> =120 @ 0.8 V <sub>CES</sub>	A
<b>P<sub>c</sub></b>	T <sub>C</sub> =25°C	280	W
<b>T<sub>J</sub></b> <b>T<sub>JM</sub></b> <b>T<sub>stg</sub></b>		-55...+175 175 -55...+150	°C
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10s Maximum Tab temperature for soldering SMD devices for 10s	300 260	°C °C
<b>M<sub>d</sub></b>	Mounting torque (M3)	1.13/10	Nm/lb.in.
<b>Weight</b>	Typical	6	g

(T<sub>J</sub>=25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			Unit
		min.	typ.	max.	
<b>BV<sub>CES</sub></b>	I <sub>C</sub> =1mA; V <sub>GE</sub> =0V	1200			V
<b>V<sub>GE(th)</sub></b>	I <sub>C</sub> =250uA; V <sub>CE</sub> =V <sub>GE</sub>	4.5	5.8	7.0	V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> =V <sub>CES</sub> ; T <sub>J</sub> =25°C V <sub>GE</sub> =0V; T <sub>J</sub> =125°C			250 4	uA mA
<b>I<sub>GES</sub></b>	V <sub>CE</sub> =0V; V <sub>GE</sub> =±20V			±200	nA
<b>V<sub>CE(sat)</sub></b>	I <sub>C</sub> =I <sub>C100</sub> ; V <sub>GE</sub> =15V		1.90	2.40	V



$C_{res}$			94		
$Q_g$			230		
$Q_{ge}$	$I_C=I_{C90}; V_{GE}=15V; V_{CE}=0.5V_{CES}$		30		nC
$Q_{gc}$			147		
$t_{d(on)}$	Inductive load, $T_J=25^\circ C$		62		ns
$t_{ri}$	$I_C=I_{C90}; V_{GE}=15V;$		54		ns
$t_{d(off)}$	$V_{CE}=0.5V_{CES}; R_G=R_{off}=10\Omega$		260		ns
$t_{fi}$	Remarks: Switching times may increase for $V_{CE( Clamp )} > 0.8V_{CES}$ higher $T_J$ or increased $R_G$		30		ns
$E_{off}$			1.4		mJ
$t_{d(on)}$	Inductive load, $T_J=150^\circ C$		55		ns
$t_{ri}$	$I_C=I_{C100}; V_{GE}=15V;$		54		ns
$E_{on}$	$V_{CE}=0.5V_{CES}; R_G=R_{off}=10\Omega$		3.5		mJ
$t_{d(off)}$	Remarks: Switching times may increase for $V_{CE( Clamp )} > 0.8V_{CES}$ higher $T_J$ or increased $R_G$		300		ns
$t_{fi}$			38		ns
$E_{off}$			1.85		mJ
$R_{thJC}(IGBT)$				0.45	$^\circ C/W$
$R_{thJA}(IGBT)$				40	$^\circ C/W$

### Reverse Diode (FRED)

( $T_J=25^\circ C$ , unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			Unit
		min.	typ.	max.	
$V_F$	$I_F=40A; T_{VJ}=150^\circ C$ $T_{VJ}=25^\circ C$		2.6 3.3		V
$I_{RM}$	$V_R=100V; I_F=40A; -di_F/dt=100A/us$ $L \leq 0.05uH; T_{VJ}=100^\circ C$		7.4		A
$t_{rr}$	$I_F=1A; -di/dt=50A/us; V_R=30V; T_J=25^\circ C$		70		ns
$R_{thJC}$	Diode			0.40	K/W



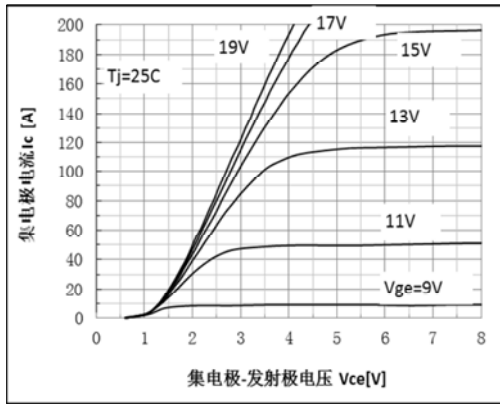


图 1 输出特性曲线

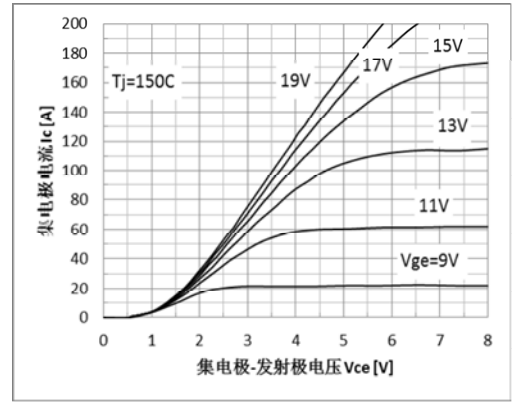


图 2 输出特性曲线

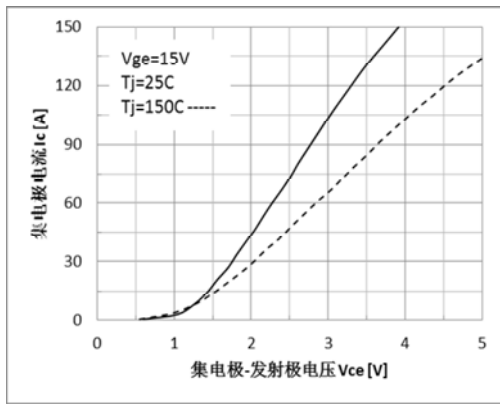


图 3 饱和和压降特性

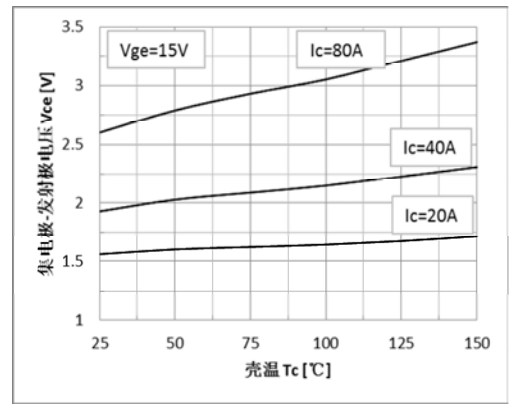


图 4 饱和和压降温度特性



图 5 电容特性

图 6 栅电荷特性

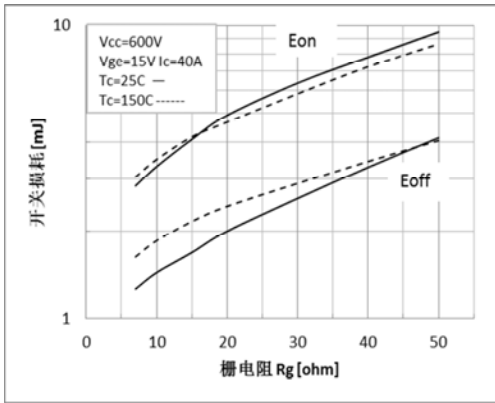


图 7 开关损耗-栅电阻特性曲线

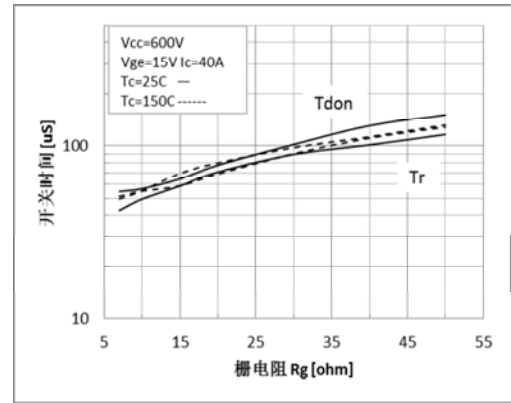


图 8 开通-栅电阻特性曲线

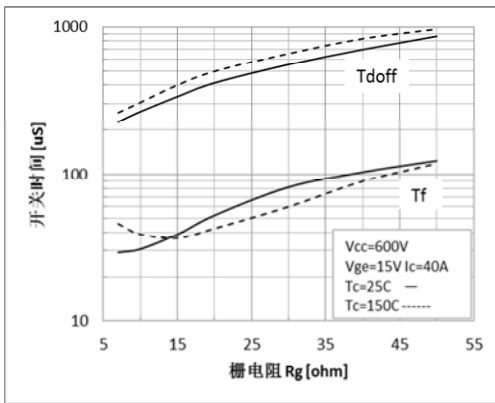


图 9 关断-栅电阻特性曲线

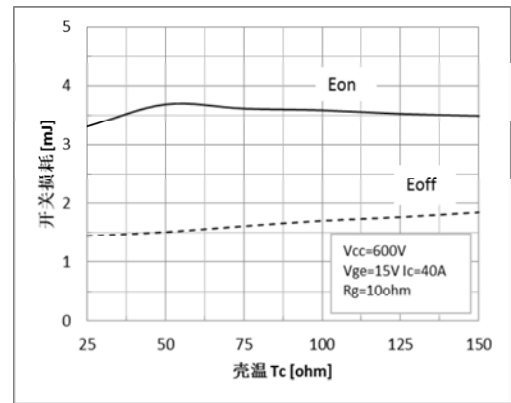


图 10 开关损耗温度特性

图 11 开通温度特性

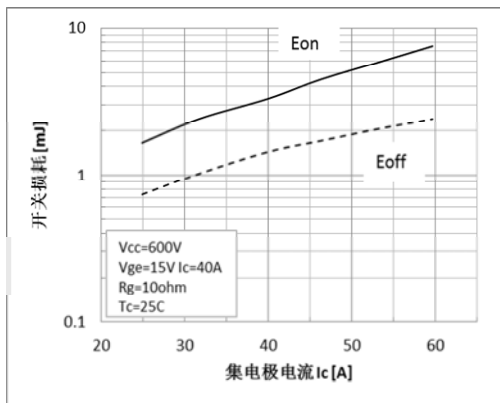


图 13 开关损耗与电流特性

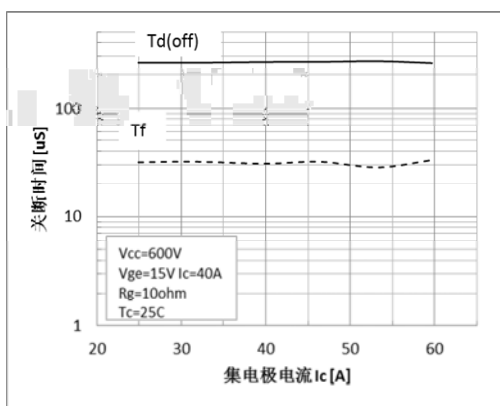


图 15 关断与电流特性

图 12 关断温度特性

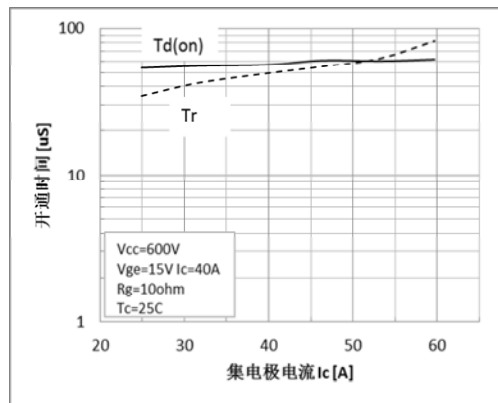


图 14 开通与电流特性

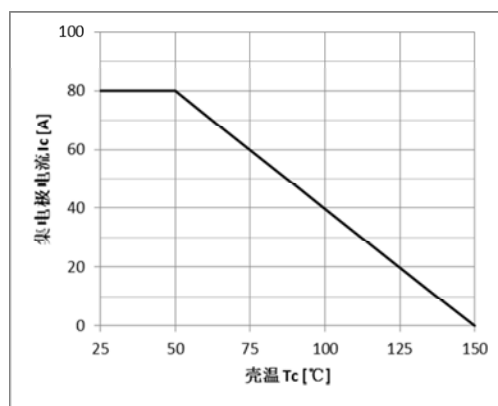


图 16 集电极电流温度特性

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图 17 正向安全工作区

图 18 二极管正向特性

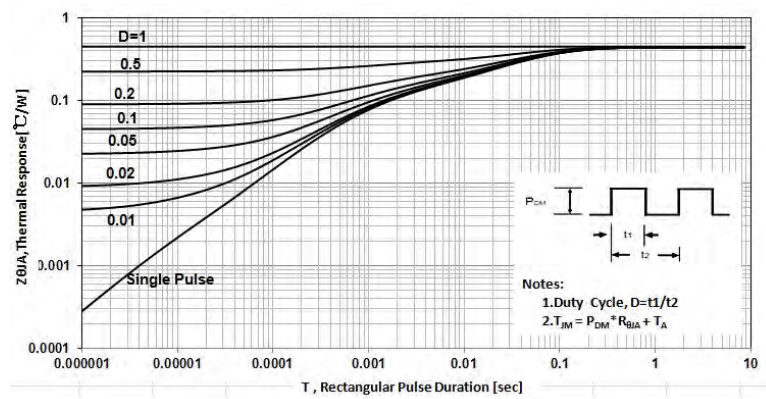
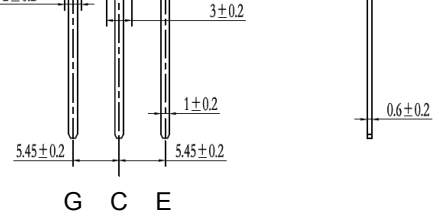


图 19 瞬态热阻特性

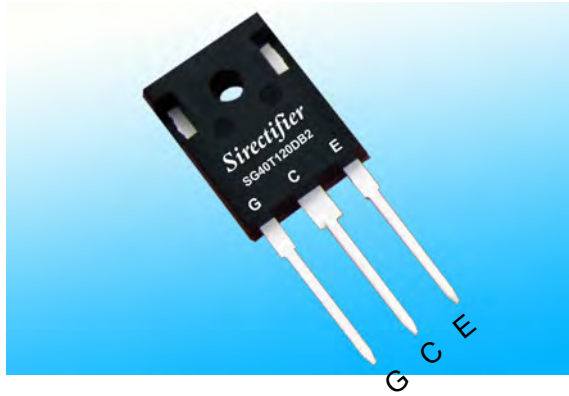




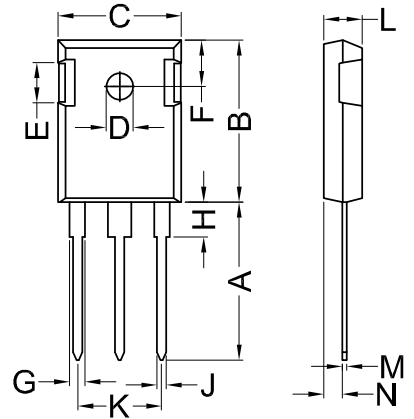
SG40T120UDB1 (封装外形 TO-3P)



TO-247AD



SG40T120UDB2 (封装外形TO-247AD)

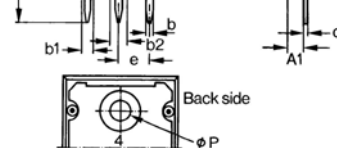


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
ØD	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.3	0.212	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.5	0.149	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.1	0.426	0.437
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102



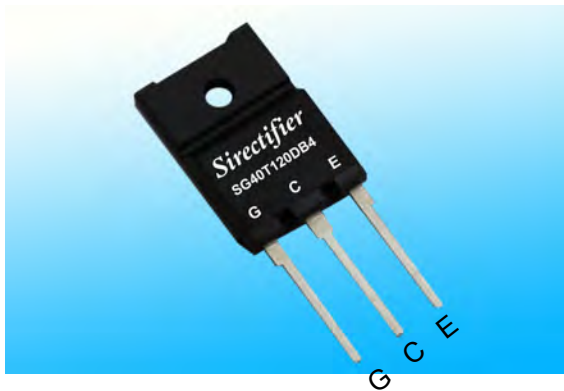


SG40T120UDB3 (封装外形TO-264)

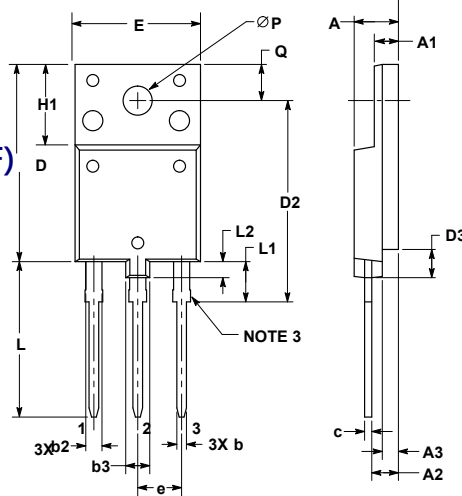


K	0.00	0.25
L	20.32	20.83
L1	2.29	2.59
P	3.17	3.66
Q	6.07	6.27
Q1	8.38	8.69
R	3.81	4.32
R1	1.78	2.29
S	6.04	6.30
T	1.57	1.83

TO-3PF



SG40T120UDB4 (封装外形绝缘式TO-3PF)



DIM	MILLIMETERS	
	MIN	MAX
A	5.30	5.70
A1	2.80	3.20
A2	3.10	3.50
A3	1.80	2.20
b	0.65	0.95
b2	1.90	2.15
b3	3.80	4.20
c	0.80	1.10
D	24.30	24.70
D2	24.70	25.30
D3	3.30	3.70
E	15.30	15.70
e	5.35	5.55
H1	9.80	10.20
L	19.10	19.50
L1	4.80	5.20
L2	1.90	2.20
P	3.40	3.80
Q	4.30	4.70





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